

MOSFETs Silicon N-Channel MOS

# SSM6K217FE

#### 1. Applications

- · Power Management Switches
- · DC-DC Converters

#### 2. Features

- (1) 1.8-V gate drive voltage.
- (2) Low drain-source on-resistance

:  $R_{\rm DS(ON)}$  = 155 m $\Omega$  (typ.) (@ $V_{\rm GS}$  = 8.0 V,  $I_{\rm D}$  = 1.0 A)

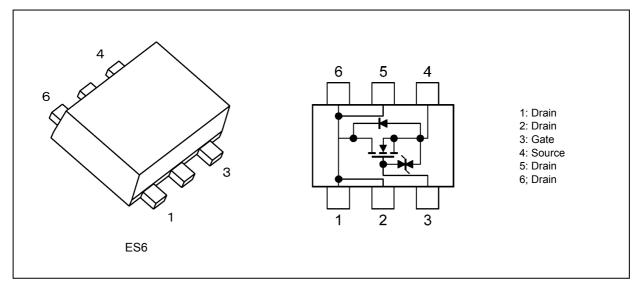
 $R_{DS(ON)} = 165 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 4.5 \text{ V}, I_D = 1.0 \text{ A})$ 

 $R_{\rm DS(ON)}$  = 170 m $\Omega$  (typ.) (@V<sub>GS</sub> = 3.6 V, I<sub>D</sub> = 1.0 A)

 $R_{DS(ON)} = 190 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 2.5 \text{ V}, I_D = 0.5 \text{ A})$ 

 $R_{DS(ON)} = 230 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 1.8 \text{ V}, I_D = 0.2 \text{ A})$ 

#### 3. Packaging and Pin Assignment





# 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	40	V
Gate-source voltage		$V_{GSS}$	±12	
Drain current (DC)	(Note 1)	$I_D$	1.8	Α
Drain current (pulsed)	(Note 1), (Note 2)	I <sub>DP</sub>	3.6	
Power dissipation	(Note 3)	$P_{D}$	500	mW
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	40	_	_	V
Drain-source breakdown voltage		V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -12 V	25	_	_	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_		1	μΑ
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	_		±10	
Gate threshold voltage	(Note 1)	$V_{th}$	$V_{DS} = 3 \text{ V}, I_{D} = 1 \text{ mA}$	0.5		1.2	V
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 8.0 V		155	195	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.5 V	_	165	208	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.2 V	_	166	211	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 3.6 V	_	170	218	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 2.5 V	_	190	248	
			I <sub>D</sub> = 0.2 A, V <sub>GS</sub> = 1.8 V	_	230	400	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_{D} = 0.2 \text{ A}$	_	2	_	S

Note 1: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

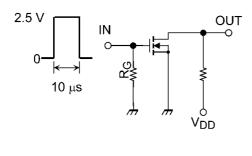
Take this into consideration when using the device.

Note 2: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	_	130	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	7.5	_	
Output capacitance	C <sub>oss</sub>		_	26	_	
Switching time (turn-on time)		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A,	_	13		ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS} = 0 \text{ to } 2.5 \text{ V}, R_{G} = 4.7 \Omega$	_	8	_	

#### 5.3. Switching Time Test Circuit



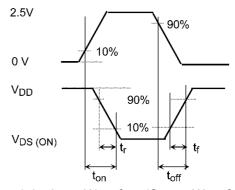


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DS}$ = 10 V, $I_{D}$ = 1.8 A,	_	1.1	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{GS} = 4.2 \text{ V}$	_	0.18	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.5	_	



# 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -2 A, V_{GS} = 0 V$	_	-0.85	-1.2	V

Note 1: Pulse measurement.

## 6. Marking

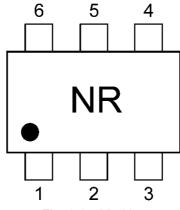


Fig. 6.1 Marking

#### 7. Characteristics Curves (Note)

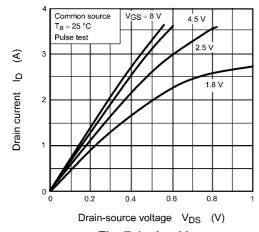


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

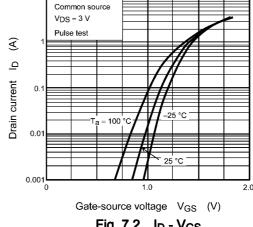


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

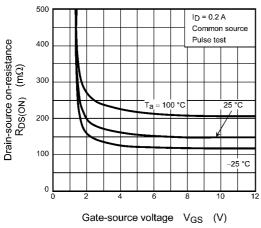


Fig. 7.3  $R_{DS(ON)} - V_{GS}$ 

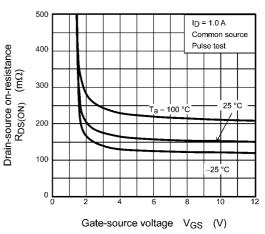


Fig. 7.4  $R_{DS(ON)}$  -  $V_{GS}$ 

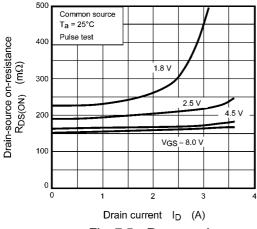


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

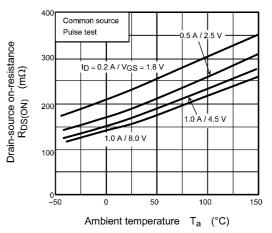


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

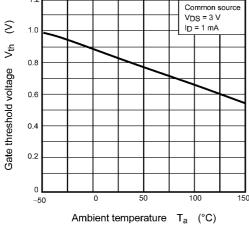


Fig. 7.7 V<sub>th</sub> - T<sub>a</sub>

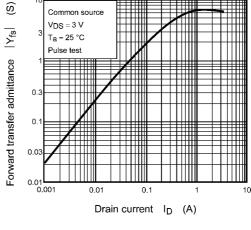


Fig. 7.8 |Y<sub>fs</sub>| - I<sub>D</sub>

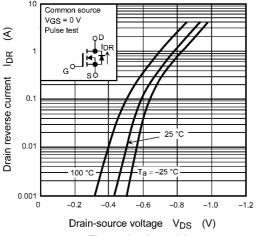


Fig. 7.9 IDR - VDS

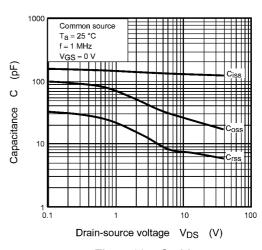


Fig. 7.10 C - V<sub>DS</sub>

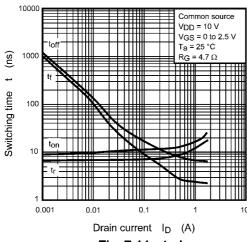


Fig. 7.11 t-I<sub>D</sub>

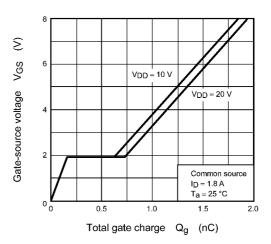
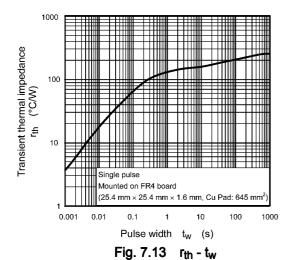


Fig. 7.12 Dynamic Input Characteristics



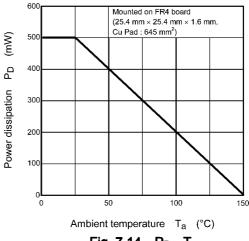


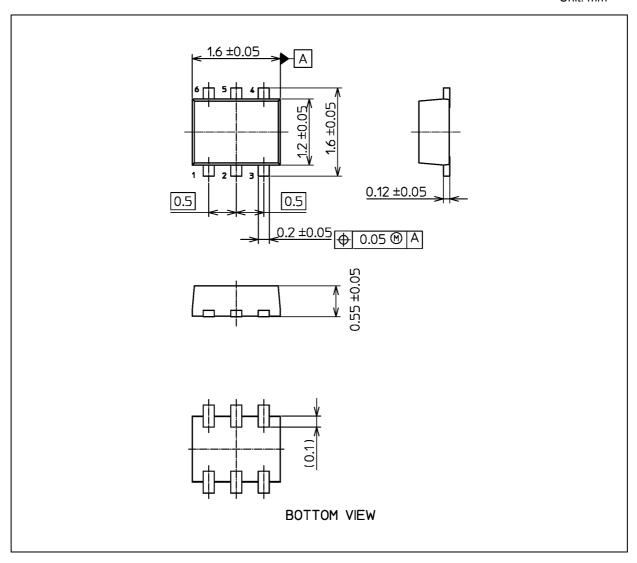
Fig. 7.14 PD - Ta

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 3.0 mg (typ.)

	Package Name(s)	
Nickname: ES6		



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